Silizium-PIN-Fotodiode mit sehr kurzer Schaltzeit
Silicon PIN Photodiode with Very Short Switching Time

SFH 203
SFH 203 FA

SFH 203

SFH 203 FA

Wesentliche Merkmale

- Speziell geeignet für Anwendungen im Bereich von 400 nm bis 1100 nm (SFH 203) und bei 880 nm (SFH 203 FA)
- Kurze Schaltzeit (typ. 5 ns)
- 5 mm-Plastikbauform im LED-Gehäuse
- Auch gegurtet lieferbar

Features

- Especially suitable for applications from 400 nm to 1100 nm (SFH 203) and of 880 nm (SFH 203 FA)
- Short switching time (typ. 5 ns)
- 5 mm LED plastic package
- Also available on tape and reel

Anwendungen

- Industrieelektronik
- „Messen/Steuern/Regeln“
- Schnelle Lichtschranken für Gleich- und Wechsellichtbetrieb
- LWL

Applications

- Industrial electronics
- For control and drive circuits
- Photointerrupters
- Fiber optic transmission systems

Typ Type	Bestellnummer Ordering Code
SFH 203	Q62702-P955
SFH 203 FA	Q62702-P956

Grenzwerte
Maximum Ratings

Bezeichnung **Parameter**	**Symbol** **Symbol**	**Wert** **Value**	**Einheit** **Unit**
Betriebs- und Lagertemperatur Operating and storage temperature range	T_{op}; T_{stg}	– 40 … + 100	°C
Löttemperatur (Lötstelle 2 mm vom Gehäuse entfernt bei Lötzeit $t \leq 3$ s) Soldering temperature in 2 mm distance from case bottom ($t \leq 3$ s)	T_S	230	°C
Sperrspannung Reverse voltage	V_R	50	V
Verlustleistung Total power dissipation	P_{tot}	100	mW

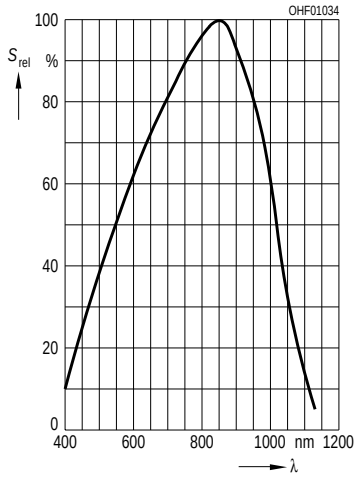
Kennwerte (T_A = 25 °C)
Characteristics

Bezeichnung **Parameter**	**Symbol** **Symbol**	**Wert** **Value**		**Einheit** **Unit**
		SFH 203	**SFH 203 FA**	
Fotostrom Photocurrent V_R = 5 V, Normlicht/standard light A, T = 2856 K, E_V = 1000 lx	I_P	80 (≥ 50)	–	µA
V_R = 5 V, λ = 950 nm, E_e = 1 mW/cm²	I_P	–	50 (≥ 30)	µA
Wellenlänge der max. Fotoempfindlichkeit Wavelength of max. sensitivity	$\lambda_{S\ max}$	850	900	nm
Spektraler Bereich der Fotoempfindlichkeit S = 10% von S_{max} Spectral range of sensitivity S = 10% of S_{max}	λ	400 … 1100	800 … 1100	nm
Bestrahlungsempfindliche Fläche Radiant sensitive area	A	1	1	mm²
Abmessung der bestrahlungsempfindlichen Fläche Dimensions of radiant sensitive area	$L \times B$ $L \times W$	1 × 1	1 × 1	mm × mm
Abstand Chipoberfläche zu Gehäuseoberfläche Distance chip front to case surface	H	4.0 … 4.6	4.0 … 4.6	mm
Halbwinkel Half angle	φ	± 20	± 20	Grad deg.

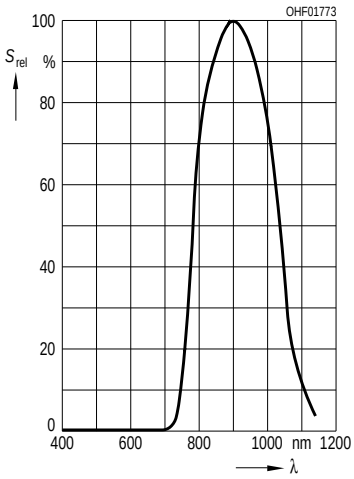
Kennwerte (T_A = 25 °C)
Characteristics (cont'd)

Bezeichnung **Parameter**	**Symbol** **Symbol**	**Wert** **Value**		**Einheit** **Unit**
		SFH 203	**SFH 203 FA**	
Dunkelstrom, V_R = 20 V Dark current	I_R	1 (≤ 5)	1 (≤ 5)	nA
Spektrale Fotoempfindlichkeit, λ = 850 nm Spectral sensitivity	S_λ	0.62	0.59	A/W
Quantenausbeute, λ = 850 nm Quantum yield	η	0.89	0.86	Electrons Photon
Leerlaufspannung Open-circuit voltage E_v = 1000 lx, Normlicht/standard light A, T = 2856 K E_e = 0.5 mW/cm², λ = 950 nm	V_O V_O	420 (≥ 350) –	– 370 (≥ 300)	mV mV
Kurzschlußstrom Short-circuit current E_v = 1000 lx, Normlicht/standard light A, T = 2856 K E_e = 0.5 mW/cm², λ = 950 nm	I_{SC} I_{SC}	80 –	– 25	µA µA
Anstiegs- und Abfallzeit des Fotostromes Rise and fall time of the photocurrent R_L = 50 Ω; V_R = 20 V; λ = 850 nm; I_p = 800 µA	t_r, t_f	5	5	ns
Durchlaßspannung, I_F = 80 mA, E = 0 Forward voltage	V_F	1.3	1.3	V
Kapazität, V_R = 0 V, f = 1 MHz, E = 0 Capacitance	C_0	11	11	pF
Temperaturkoeffizient von V_O Temperature coefficient of V_O	TC_V	– 2.6	– 2.6	mV/K
Temperaturkoeffizient von I_{SC} Temperature coefficient of I_{SC} Normlicht/standard light A λ = 950 nm	TC_I	0.18 –	– 0.2	%/K
Rauschäquivalente Strahlungsleistung Noise equivalent power V_R = 20 V, λ = 850 nm	NEP	2.9×10^{-14}	2.9×10^{-14}	$\frac{W}{\sqrt{Hz}}$
Nachweisgrenze, V_R = 20 V, λ = 850 nm Detection limit	D*	3.5×10^{12}	3.5×10^{12}	$\frac{cm \times \sqrt{Hz}}{W}$

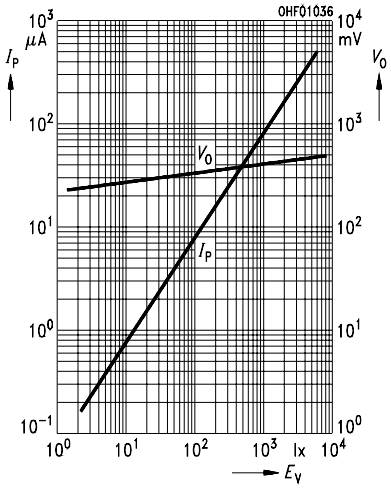
Relative Spectral Sensitivity
SFH 203
$S_{rel} = f(\lambda)$



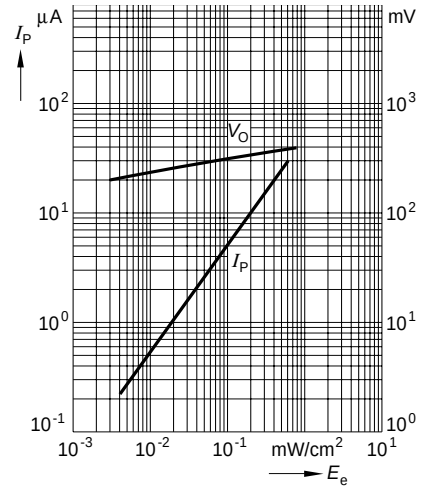
Relative Spectral Sensitivity
SFH 203 FA
$S_{rel} = f(\lambda)$



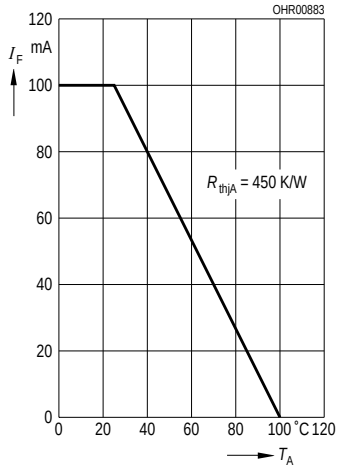
Photocurrent $I_P = f(E_v)$, V_R = 5 V
Open-Circuit Voltage $V_O = f(E_v)$
SFH 203



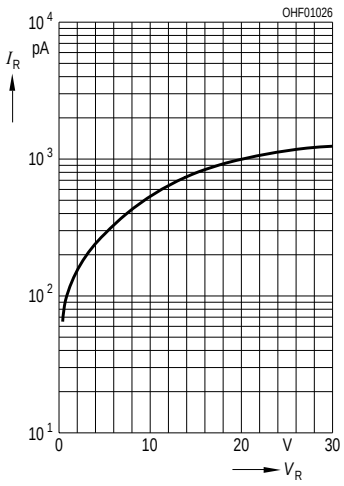
Photocurrent $I_P = f(E_e)$, V_R = 5 V
Open-Circuit-Voltage $V_O = f(E_e)$
SFH 203 FA



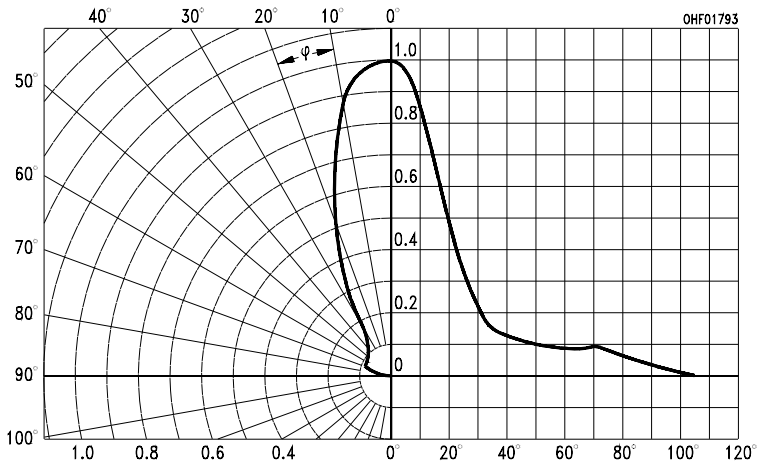
Total Power Dissipation
$P_{tot} = f(T_A)$



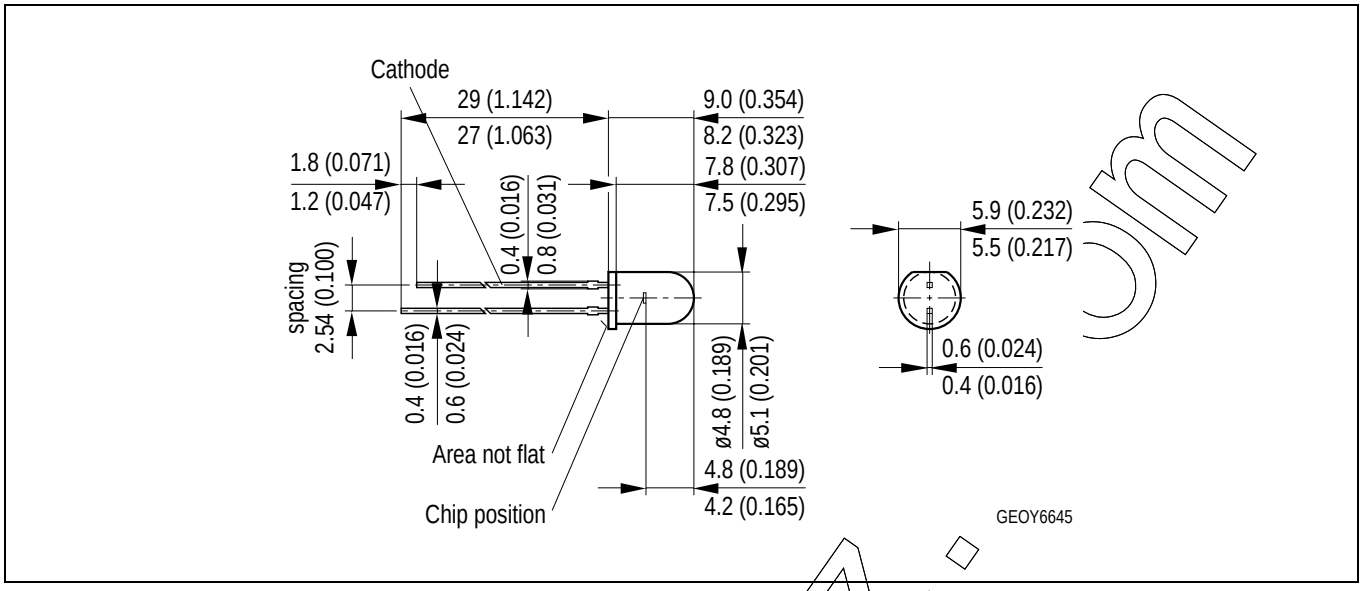
Dark Current
$I_R = f(V_R)$, E = 0



Directional Characteristics
$S_{rel} = f(\varphi)$



Maßzeichnung
Package Outlines



Maße werden wie folgt angegeben: mm (inch) / Dimensions are specified as follows: mm (inch).

Published by OSRAM Opto Semiconductors GmbH & Co. OHG
Wernerwerkstrasse 2, D-93049 Regensburg

Attention please!

The information describes the type of component and shall not be considered as assured characteristics.
Terms of delivery and rights to change design reserved. Due to technical requirements components may contain dangerous substances. For information on the types in question please contact our Sales Organization.

Packing

Please use the recycling operators known to you. We can also help you – get in touch with your nearest sales office. By agreement we will take packing material back, if it is sorted. You must bear the costs of transport. For packing material that is returned to us unsorted or which we are not obliged to accept, we shall have to invoice you for any costs incurred.

Components used in life-support devices or systems must be expressly authorized for such purpose! Critical components [1] may only be used in life-support devices or systems [2] with the express written approval of OSRAM OS.

[1] A critical component is a component used in a life-support device or system whose failure can reasonably be expected to cause the failure of that life-support device or system, or to affect its safety or effectiveness of that device or system.

[2] Life support devices or systems are intended (a) to be implanted in the human body, or (b) to support and/or maintain and sustain human life. If they fail, it is reasonable to assume that the health of the user may be endangered.